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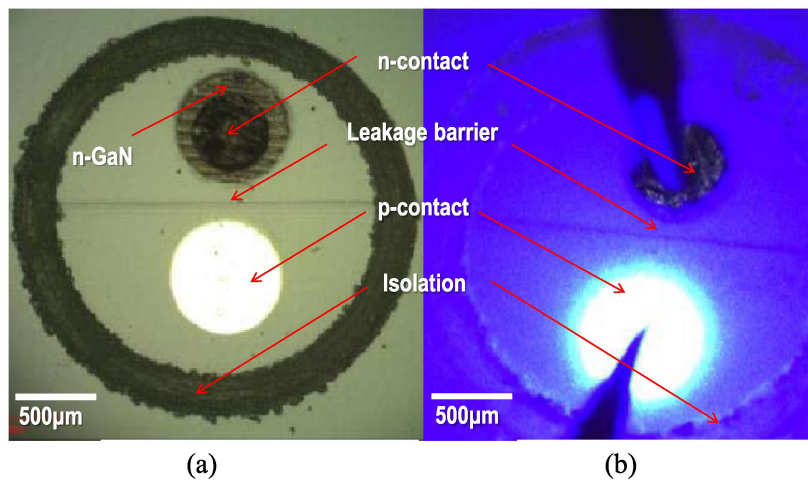
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(a) The image of the Q-check pattern on the wafer and (b) its EL image under forward bias (Shim *et al.*, Article #3300406).

*For the November 2016 issue, see Article #0101101 for the Table of Contents.
For the December 2016 issue, see Article #0101201 for the Table of Contents.*

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VOLUME 52

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REGULAR PAPERS

<i>Mode-Locked Lasers</i>	
Amplitude and Phase Noise of Frequency Combs Generated by Single-Section InAs/InP Quantum-Dash-Based Passively and Actively Mode-Locked Lasers	V. Panapakkam, A. P. Anthur, V. Vujicic, R. Zhou, Q. Gaimard, K. Merghem, G. Aubin, F. Lelarge, E. A. Viktorov, L. P. Barry, and A. Ramdane 1300207
<i>Laser Applications</i>	
Frequency Measurement of Far-Infrared Laser Emissions Generated by C-13 Methanol Isotopologues	M. Jackson, B. Freeman, M. Smith, and M. Kemper 1400104
<i>Fiber Lasers</i>	
Numerical Modeling of 3.5 μm Dual-Wavelength Pumped Erbium-Doped Mid-Infrared Fiber Lasers	A. Malouf, O. Henderson-Sapir, M. Gorjan, and D. J. Ottaway 1600412
<i>Semiconductor Lasers</i>	
Dynamics and Stability of Mutually Coupled Nano-Lasers	H. Han and K. A. Shore 2000306
<i>Surface-Emitting Semiconductor Lasers</i>	
850-nm VCSELs With p-Type δ -Doping in the Active Layers for Improved High-Speed and High-Temperature Performance	K.-L. Chi, D.-H. Hsieh, J.-L. Yen, X.-N. Chen, J. Chen, H.-C. Kuo, Y.-J. Yang, and J.-W. Shi 2400607
Polarization Switching Characteristics of 1550-nm Vertical-Cavity Surface-Emitting Lasers Subject to Double Polarization Pulsed Injection	B. Jiang, Z.-M. Wu, T. Deng, J.-J. Chen, F. Yang, J. Chen, Q. Liang, and G.-Q. Xia 2400707
Analysis of Threshold Currents and Transverse Modes in Nitride VCSELs With Different Resonators	P. Śpiewak, M. Marciniak, M. Wasiaik, W. Nakwaski, and R. P. Sarzala 2400807
<i>Short-Wavelength Light Emitting Diodes</i>	
Wafer-Level Electroluminescence Metrology for InGaN Light-Emitting Diodes	J.-I. Shim, D.-P. Han, and D.-S. Shin 3300406
<i>Photodetectors</i>	
Resonant Cavity Enhanced Thyristor-Based Photodetectors for Optical Receivers	B. C. Pile and G. W. Taylor 4000404
<i>Photodiodes</i>	
AlGaAs/GaAs Triple Quantum Well Photodetector at 5 μm Wavelength—A Simulation Study	C. Tang, Y. Lan, M. Dutta, M. A. Stroschio, and J. Shi 4400108
<i>Optical Communication</i>	
Testing Random-Detector-Efficiency Countermeasure in a Commercial System Reveals a Breakable Unrealistic Assumption	A. Huang, S. Sajeed, P. Chaiwongkhot, M. Soucarros, M. Legré, and V. Makarov 8000211
<i>Multiwave Mixing</i>	
Isolation of Weak Four-Wave Mixing Signal Components in Reflection Experiments	T. W. Jarvis 9100108